

In the Specification:

Please rewrite the last paragraph on page 5 to read as follows:

Following creation of the mask, which can be done using conventional processes, doping is done, preferably an implantation of phosphorous ions at a dose of, for example, 2×10^{13} atoms/cm², in order to create an n-doped trough 5 in the semiconductor substrate 1. The implantation energy in this process is such that over the trough 5 in the semiconductor substrate 1 there still remains a weakly p-doped inner area 6. At a dose of 2×10^{13} atoms/cm² this is, despite the back-scattered phosphorous ions, for example, the case if the implantation energy is 6 MeV phosphorous ions.